

a second diffusion region formed in the layer adjacent to and spaced apart from the first diffusion region;

a channel region formed at a boundary between the first and second diffusion regions, wherein said channel region is bounded by first and second diffusion edges of the first diffusion region; and

at least one island formed at least partially in the first diffusion region, the at least one island being positioned non-symmetrically about a plane perpendicular to a top surface of the semiconductor layer and perpendicular to the boundary, wherein said plane bisects the channel region.

101. (Amended) The ESD protection device of claim 1, wherein said at least one island having a first island edge near said first diffusion edge and a second island edge near said second diffusion edge;

a first gap of at least zero spacing between the first diffusion edge and a first nearest island edge;

a second gap of at least zero spacing between the second diffusion edge and a second nearest island edge; and said first gap being larger than the second gap.

102. (Amended) An electrostatic discharge (ESD) protection device, comprising:

a semiconductor layer;

a first diffusion region formed in the layer;

a second and a third diffusion region formed in the layer each adjacent to and spaced apart from the first diffusion region;

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